

Appl. No. : 10/074,564
Filed : February 11, 2002

A1 can be used to make various useful structures such as wetting layers, HSG silicon, quantum dots, dielectric layers, anti-reflective coatings (ARC's), gate electrodes and diffusion sources.

IN THE SPECIFICATION:

Please replace paragraph [0001] with the following rewritten paragraph:

A2 [0001] This application claims priority to U.S. Provisional Application No. 60/268,337, filed February 12, 2001; U.S. Provisional Application No. 60/279,256, filed March 27, 2001; U.S. Provisional Application No. 60/311,609, filed August 9, 2001; U.S. Provisional Application No. 60/323,649, filed September 19, 2001; U.S. Provisional Application No. 60/332,696, filed November 13, 2001; U.S. Provisional Application No. 60/333,724, filed November 28, 2001; and U.S. Provisional Application No. 60/340,454, filed December 7, 2001; all of which are hereby incorporated by reference in their entireties. This application is related to, and incorporates by reference in their entireties, co-owned and co-pending U.S. Patent Application Serial Numbers: 10/074,563; 10/074,149; 10/074,722; 10/074,633; and 10/074,534, all of which were filed on February 11, 2002.

Please delete paragraph [0002].

IN THE CLAIMS:

Please amend Claim 51 as follows:

A3 51. (Amended) An integrated circuit comprising a continuous amorphous Si-containing film having a thickness that is 15 Å or greater and that is 150 Å or less, a surface area of about one square micron or greater, and a thickness non-uniformity of about 10% or less for a mean film thickness in the range of 100 Å to 150 Å, a thickness non-uniformity of about 15% or less for a mean film thickness in the range of 50 Å to 99 Å, and a thickness non-uniformity of about 20% or less for a mean film thickness of less than 50 Å.